TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

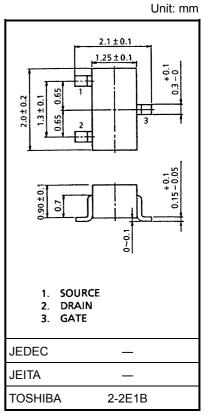
# 2SK1875

High Frequency Amplifier Applications AM High Frequency Amplifier Applications Audio Frequency Amplifier Applications

- High  $|Y_{fs}|$ :  $|Y_{fs}| = 25 \text{ mS (typ.)}$
- Low  $C_{iss}$ :  $C_{iss} = 7.5 \text{ pF}$  (typ.)

### Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V <sub>GDS</sub>	-20	V
Gate current	I <sub>G</sub>	10	mA
Drain power dissipation	PD	100	mW
Junction temperature	Тј	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C



Weight: 0.006 g (typ.)

#### **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = -15 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	_		-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS} = 0 \text{ V}, \text{ I}_{G} = -100 \mu\text{A}$	-20	_	_	V
Drain current	I <sub>DSS</sub> (Note)	$V_{DS} = 5 V, V_{GS} = 0 V$	6	_	32	mA
Gate-source cut-off voltage	V <sub>GS (OFF)</sub>	$V_{DS} = 5 \text{ V}, \text{ I}_D = 1 \mu \text{A}$	_		-2.5	V
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$	15	25	_	mS
Input capacitance	C <sub>iss</sub>	$V_{DS} = 5 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	_	7.5	10	pF
Reverse transfer capacitance	C <sub>rss</sub>	$V_{DG} = 5 \text{ V}, \text{ I}_D = 0 \text{ A}, \text{ f} = 1 \text{ MHz}$	_	2	3	pF

Note: IDSS classification

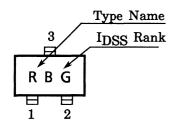
GR: 6~12 mA, BL: 10~20 mA, V: 16~32 mA

(G) (L) (V)

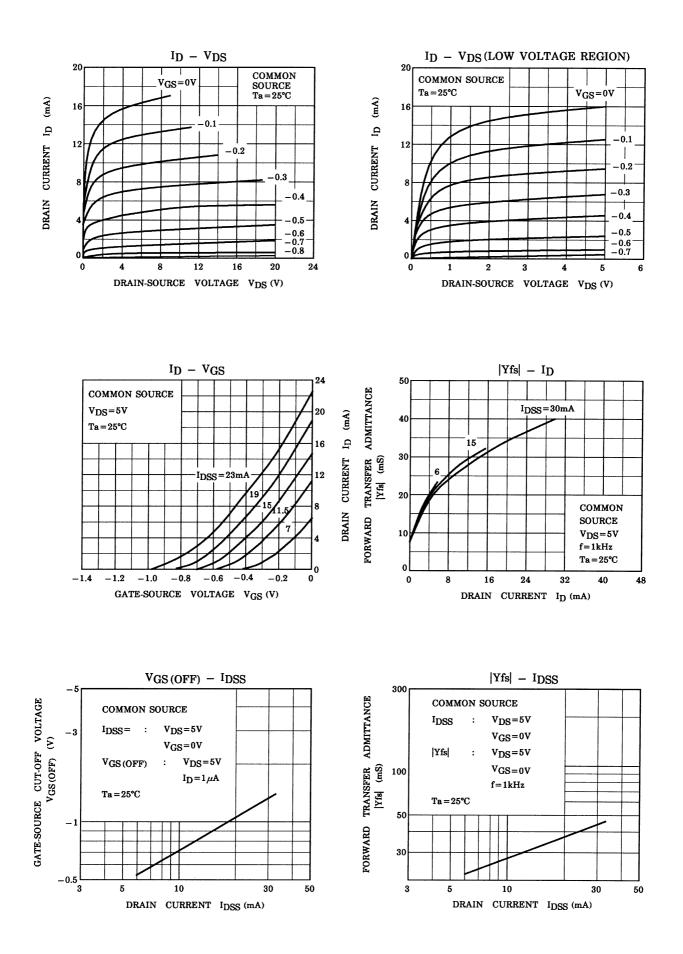
( ).....  $I_{\mbox{DSS}}$  rank marking

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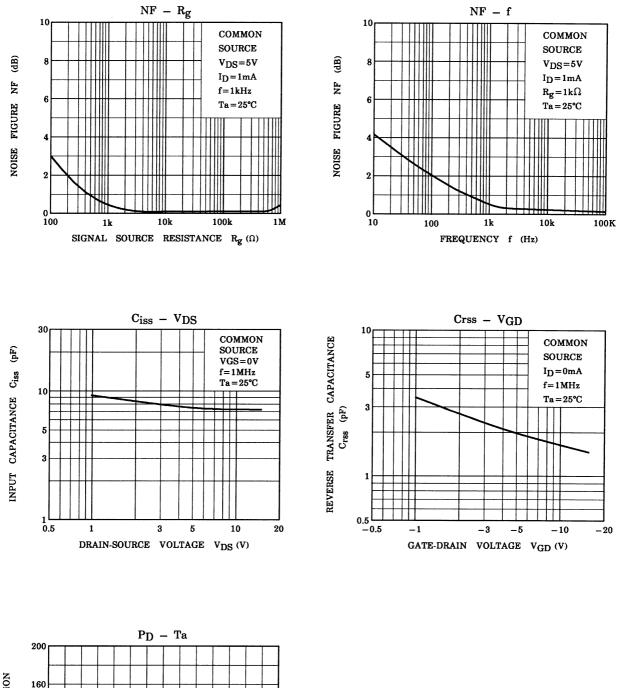
## Marking

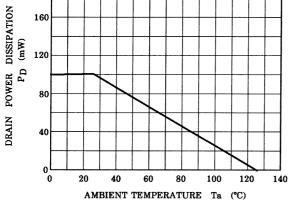


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